

2SK1669

Silicon N-Channel MOS FET

HITACHI

ADE-208-1310 (Z)

1st. Edition

Mar. 2001

Application

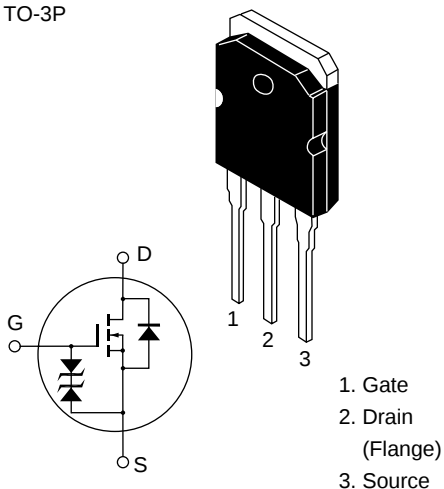
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- Built-in fast recovery diode ($t_{rr} = 90 \text{ ns}$)
- Suitable for motor control, switching regulator and DC – DC converter

Outline

TO-3P



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	250	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I_D	30	A
Drain peak current	$I_{D(pulse)}^{*1}$	120	A
Body to drain diode reverse drain current	I_{DR}	30	A
Channel dissipation	P_{ch}^{*2}	125	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

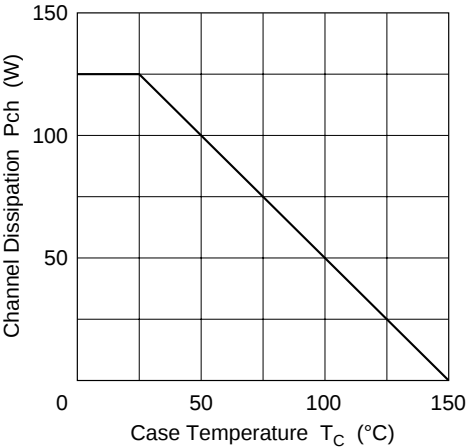
Notes 1. PW 10 μs, duty cycle 1%
2. Value at T_c = 25°C

Electrical Characteristics (Ta = 25°C)

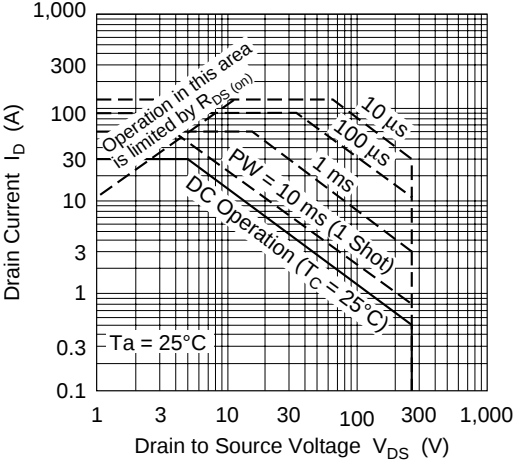
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	250	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	—	—	V	$I_G = \pm 100 \text{ } \mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	250	μA	$V_{DS} = 200 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.075	0.095		$I_D = 15 \text{ A}$, $V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	12	20	—	S	$I_D = 15 \text{ A}$, $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	Ciss	—	3100	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	Coss	—	1330	—	pF	
Reverse transfer capacitance	Crss	—	190	—	pF	
Turn-on delay time	$t_{d(on)}$	—	45	—	ns	$I_D = 15 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_L = 2$
Rise time	t_r	—	170	—	ns	
Turn-off delay time	$t_{d(off)}$	—	270	—	ns	
Fall time	t_f	—	150	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 30 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	90	—	ns	$I_F = 30 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note 1. Pulse test

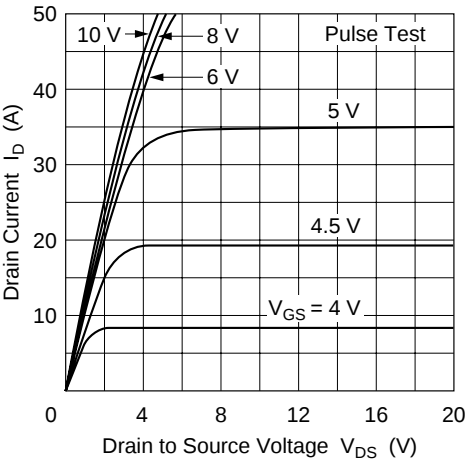
Power vs. Temperature Derating



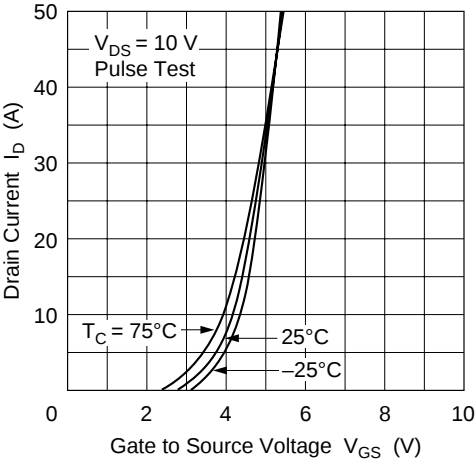
Maximum Safe Operation Area

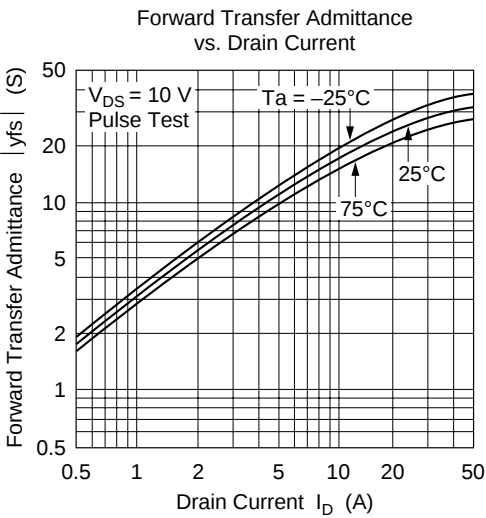
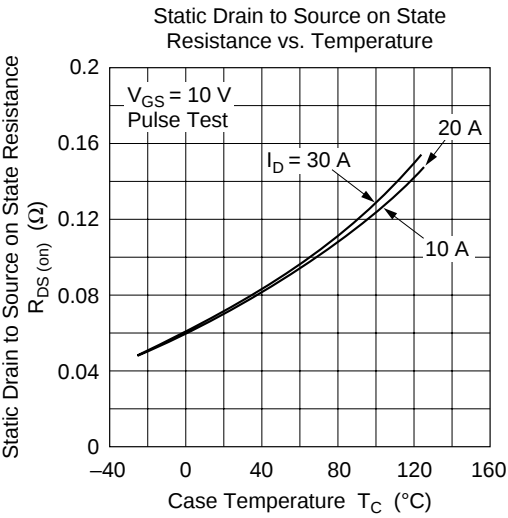
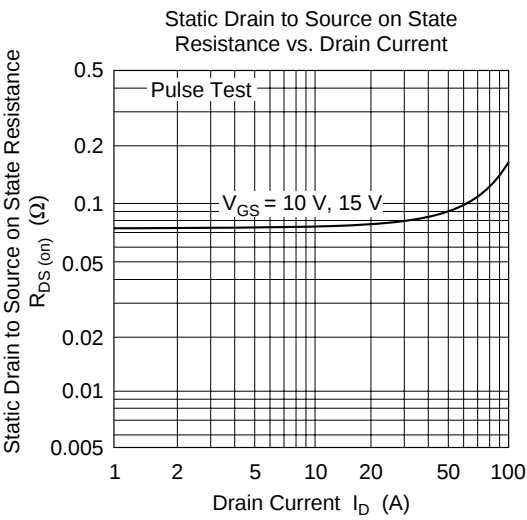
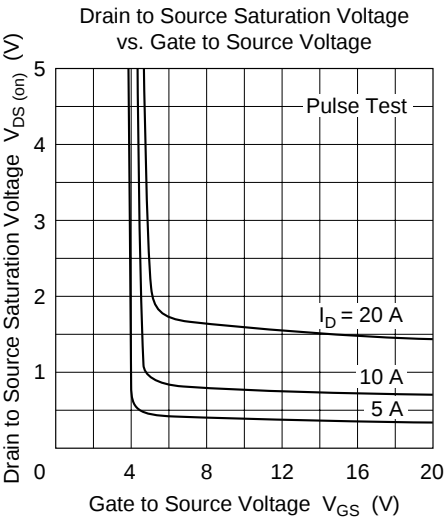


Typical Output Characteristics

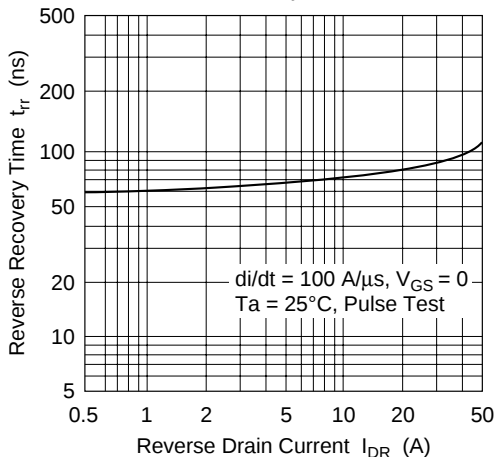


Typical Transfer Characteristics

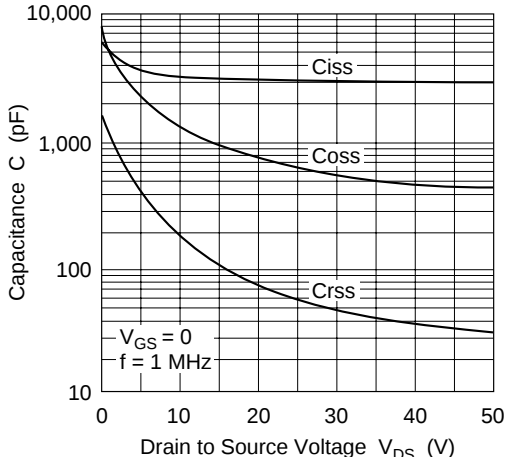




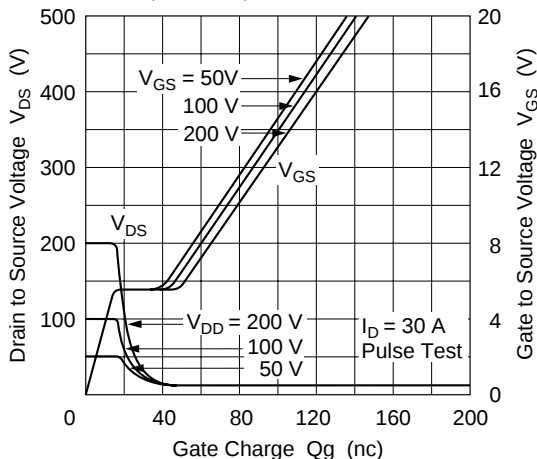
Body to Drain Diode Reverse Recovery Time



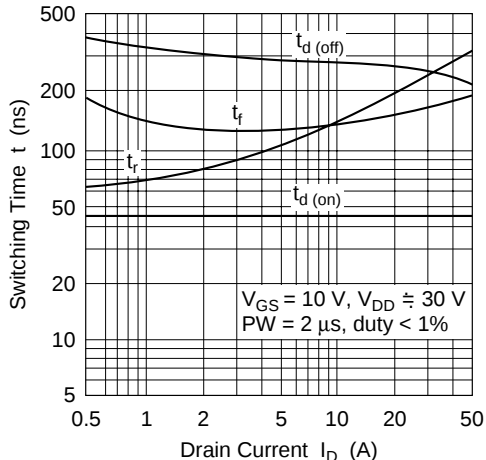
Typical Capacitance vs. Drain to Source Voltage

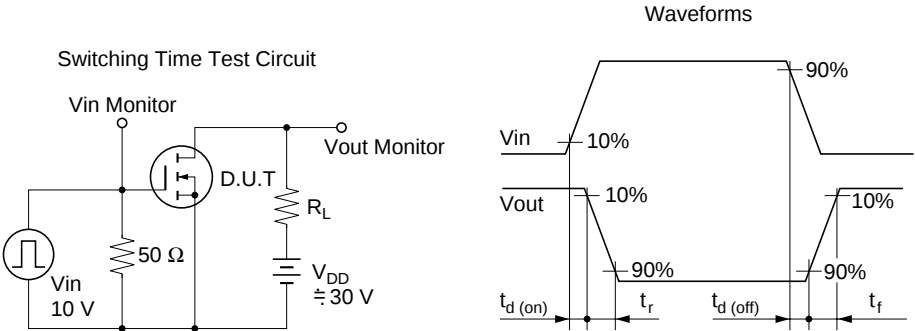
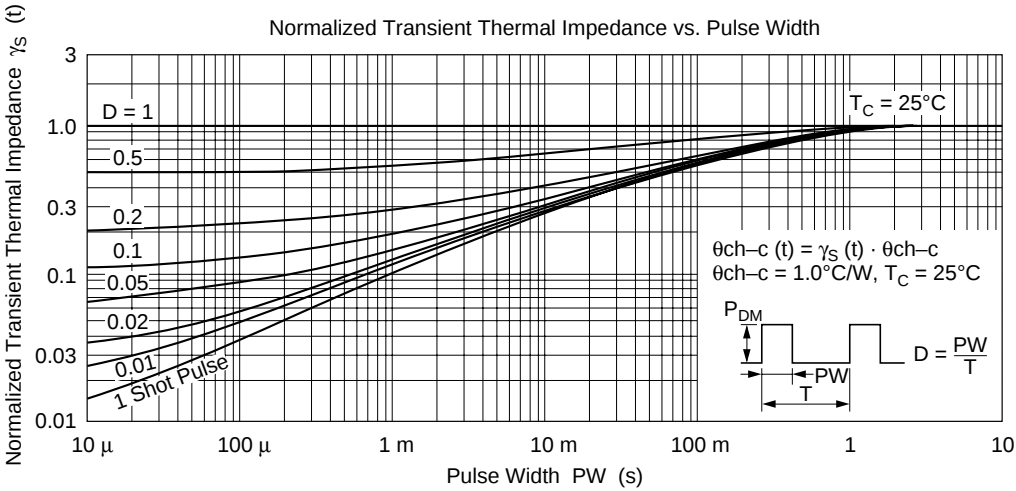
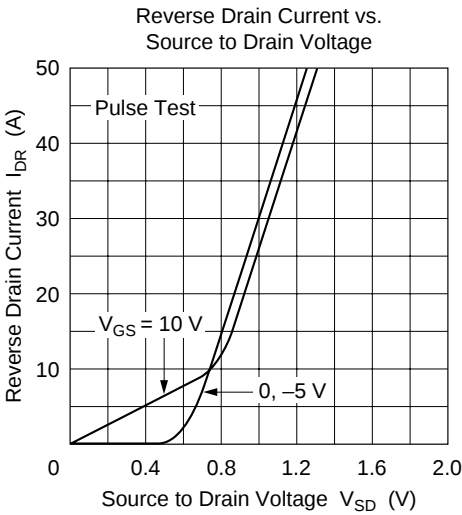


Dynamic Input Characteristics



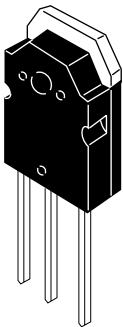
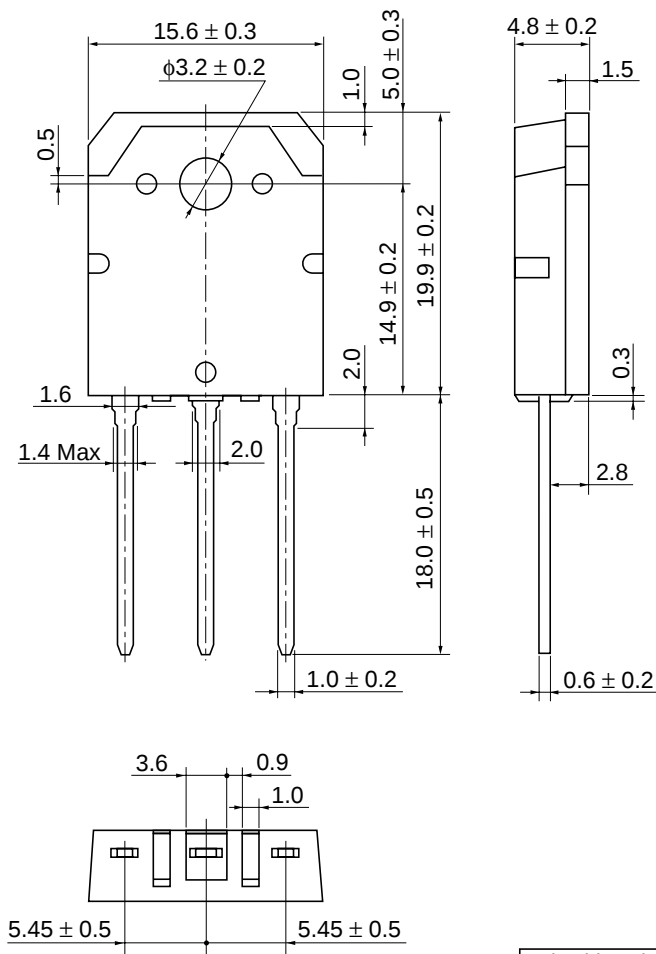
Switching Characteristics





Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Mass (reference value)	5.0 g

Cautions

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